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# N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A)		
150	0.241 at $V_{GS} = 10 \text{ V}$	6		
	0.250 at V <sub>GS</sub> = 4.5 V	4		

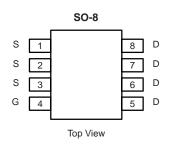
#### **FEATURES**

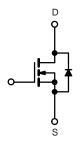
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested



#### **APPLICATIONS**

· Primary Side Switch





N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	150	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	v			
0 11 D 1 0 1 17 17 20 b	T <sub>C</sub> = 25 °C	1	6			
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 125 °C	l <sub>D</sub> –	4.7			
Pulsed Drain Current	I <sub>DM</sub>	25	Α			
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	5.2				
Avalanche Current	I <sub>AR</sub>	4.5				
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AR</sub>	11.3	mJ		
Mariana Para Discipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	62 <sup>b</sup>	W		
Maximum Power Dissipation	T <sub>A</sub> = 25 °C		2.7 <sup>a</sup>	v		
Operating Junction and Storage Temperature Range	•	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
lumation to Amelianta	t ≤ 10 s	- R <sub>thJA</sub>	16	20	°C/W	
Junction-to-Ambient <sup>a</sup>	Steady State		45	55		
Junction-to-Case		R <sub>thJC</sub>	2	2.4		

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static	l .				L		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$				V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$				V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
	I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	1	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	15			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A		0.241	0.263	Ω	
D : 0	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A, T <sub>J</sub> = 125 °C		0.249	0.273		
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A, T <sub>J</sub> = 175 °C		0.280	0.302		
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 2 A		0.250	0.275		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 2 A		25		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			900		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		115			
Reverse Transfer Capacitance	C <sub>rss</sub>			70			
Total Gate Charge <sup>c</sup>	$Q_g$			20	25		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$		5.5		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7			
Gate Resistance	R <sub>g</sub>		1		3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	12		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		35	55	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 2 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5$		17	25	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>	Ω		30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	<sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				6	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 2 \text{ A}, V_{GS} = 0 \text{ V}$		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2 A, dI/dt = 100 A/μs		55	85	ns	

#### Notes:

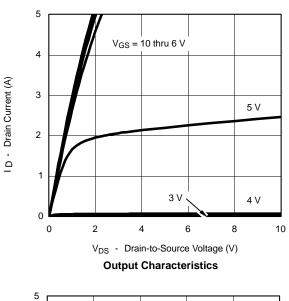
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

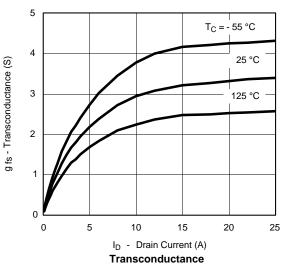
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

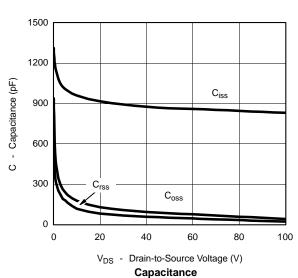


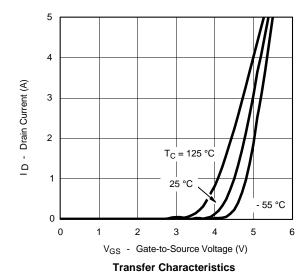
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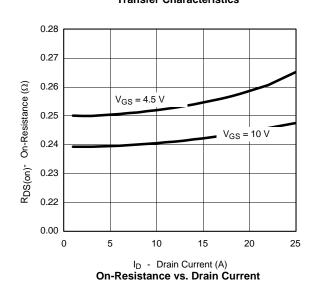
## TYPICAL CHARACTERISTICS (25 °C unless noted)

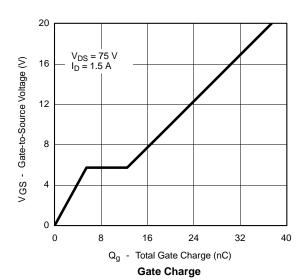








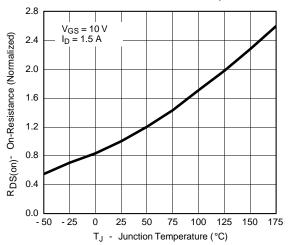






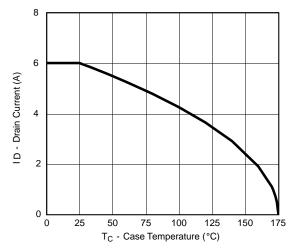


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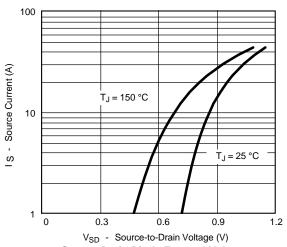


On-Resistance vs. Junction Temperature

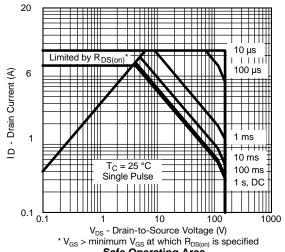
### THERMAL RATINGS



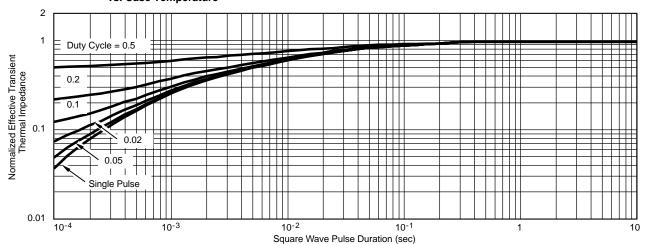
**Maximum Avalanche Drain Current** vs. Case Temperature



Source-Drain Diode Forward Voltage



\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified **Safe Operating Area** 



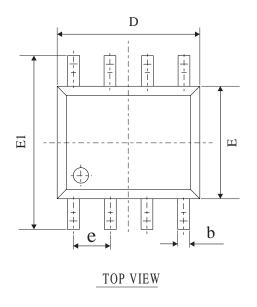
Normalized Thermal Transient Impedance, Junction-to-Case

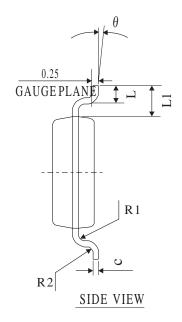


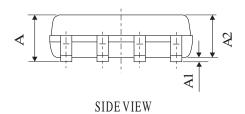
Din-Tek SEMICONDUCTOR

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# SOP-8 PACKAGE OUTLINE







COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	
A	1.30	1.60	1.85	
A1	0.03	0.15	0.28	
A2	1.20	1.45	1.70	
ь	0.26	0.40	0.54	
С	0.132	0.203	0.273	
D	4.50	4.90	5.30	
Е	3.50	3.00	4.30	
E1	5.50	6.00	6.50	
L	0.30	0.70	1.10	
θ	2°	4°	6°	
L1	1.04REF			
e	1.27BSC			
R1	0.07TYP			
R2	0.07TYP			





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